Списък на публикациите
на доц. дфзн Веселин Тодоров Дончев

O. Chapters in books

O.1. **V. Donchev**, K. Germanova, N. Shtinkov, S. J. Vlaev
”Electronic structure and optical properties of AlAs/GaAs superlattices containing embedded GaAs quantum wells with abrupt and graded interfaces”
in: *Frontal Semiconductor Research* , ed. Oliver T. Chang (Nova Science Publishers, Inc. New York, 2006) Chap. 2, pp.25-60.

O.2. V. Donchev, M. Milanova, S. Georgiev, book chapter “*Study of GaAs-Based Dilute Nitride Materials Grown by Liquid Phase Epitaxy*” in: Newest Updates in Physical Science Research (B. P. International, 2021) Vol. 7, 31–38.

A. Articles in scientific journals

A1. **V.Donchev**, K.Nanev, Chr.Tenchov
“On the interpretation of the titanium line in the appearance potential spectroscopy"
Vacuum **36**, 655-657 (1986).

A2. K.Germanova, **V.Donchev**, Ch.Hardalov, L.Nikolov
"EL2 in photoconductivity spectra of Cr-doped SI GaAs bulk crystals"
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A3. K.Germanova, **V.Donchev**, L.Nikolov
"Analysis of surface conductance in semiinsulating gallium arsenide containing deep levels in the bulk"
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A5. K.Germanova, **V.Donchev**, V.Valchev, Ch.Hardalov
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A9. S.L.Feng, J.Krynicki, **V.Donchev**, J.C.Bourgoin, M.Di Forte-Poisson, C.Brylinski, S.Delage, H.Blank, S.Alaya.
"Band Offset of GaAs-GaInP Heterojunctions"
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A10. H.Chaabane, M.Zazoui, J.C.Bourgoin, **V.Donchev**.
"Electronic Transport through Semiconductor Barriers"
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A11. K.Germanova, **V.Donchev**, I. Ivanov, N.Zheleva, Ch. Hardalov
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A12. **V.Donchev**, K.Germanova
"Time evolution of Zero-Bias photocurrent in semiinsulating GaAs:Cr"
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A13. **V.Donchev**, N.Shtinkov, K.Germanova,
"Effect of random defect density fluctuations on the Fermi level in highly compensated semiconductors"
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A14. N.Shtinkov, **V.Donchev**, K.Germanova, H.Kolev
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A15. N. Shtinkov, S.J. Vlaev, **V. Donchev**
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A16. M. Mazilu, A. Miller, **V. T. Donchev**
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“Electronic properties of AlAs/GaAs superlattices containing embedded GaAs quantum wells”
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A25. **V. Donchev**, K. Germanova, N. Shtinkov
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"Effect of the Electric Field on the Carrier Collection Efficiency of InAs/GaAs quantum dots"
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“Interdiffused InAs/InGaAlAs quantum dashes-in-well structures studied by surface photovoltage spectroscopy”
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A surface photovoltage spectroscopy study of GaAs/AlAs complicated nanostructures with graded interfaces
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A37. T. Angelova, N. Shtinkov, Ts. Ivanov, **V. Donchev**, A. Cantarero, Ch. Deneke, O. G. Schmidt, and A. Cros
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A42. Tareq Abu Hamed, ……**,V. Donchev**,…... et al.
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A43. M. Milanova, **V. Donchev**, K. L. Kostov, D. Alonso-Álvarez, P. Terziyska, G. Avdeev, E. Valcheva, K. Kirilov and S. Georgiev
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A44. **V. Donchev**
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„Surface photovoltage characterisation of metal halide perovskite on crystalline silicon using Kelvin probe force microscopy and metal-insulator-semiconductor configuration‘
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B. Conference papers published in scientific journals

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“Optical determination of interface roughness in multilayered semiconductor structures”
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B3. N.Shtinkov, S.Vlaev, **V.Donchev**, K.Germanova
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B30. Ts Ivanov, **V Donchev**, T Angelova, A Cros, A Cantarero, N Shtinkov, K Borissov, D Fuster, Y González and L González
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U13. **V. Donchev**
"Surface Photovoltage Spectroscopy – a Handy Tool For Characterization of Semiconductor Materials and Nanostructures"
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U14. **V Donchev**, I Asenova, M Milanova, D Alonso-Álvarez, K Kirilov, N Shtinkov, I G Ivanov, S Georgiev, E Valcheva and N Ekins-Daukes
„Characterization of liquid-phase epitaxy grown thick GaInAs (Sb)N layers"
(poster at PHOTONICA2017 The 6th International School and Conference on Photonics, 28.08.-01.09.2017 Belgrade, Serbia)

U15. **V.Donchev**
„Surface Photovoltage Spectroscopy Studies of Optoelectronic Materials and Nanostructures"
invited lecturer, 11th Photonic Workshop, 11-14.03.2018, Kopaonik, Serbia

U16. M. Milanova, **V. Donchev**, K. Kirilov, D. Alonso-Álvarez, M. Guina, A. Aho, B. Arnaudov, S. Georgiev, N.

Ekins-Daukes, T. Salminen, R. Isoaho, S. Mäkelä
„Low-temperature liquid-phase epitaxy growth and characterization of GaAsSbN/GaAs heterostructures for solar cell applications“
(Poster at 34th Int. Conf. of Physics of Semiconductors, 29.07-03.08.2018, Montpellier, France)

U17. **V. Donchev**
"Investigation of dilute nitrides bulk layers and heterostructures grown by LPE for solar cells applications" lecture at the 2nd workshop "Advanced Materials for the Efficient use of Energy" 28-29.10.2019, Valencia, Spain

U18. **V. Donchev**
"Surface Photovoltage Spectroscopy of Optoelectronic Materials"
lecture at GeePs, CNRS - CentraleSupélec - Université Paris Saclay, Oct.,2021)

U19. **V. Donchev**
"Surface Photovoltage Spectroscopy -Physics and Applications"
lecture at Insitute Photovoltaic de France, Paris, Oct.,2021)